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# IMPORTANT NOTICE

10 December 2015

## 1. Global joint venture starts operations as WeEn Semiconductors

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As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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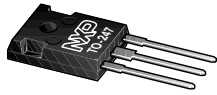
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Thank you for your cooperation and understanding,

WeEn Semiconductors



# BYV430W-300P

Dual ultrafast power diode

1 September 2015

Product data sheet

## 1. General description

2x30A, 300V dual ultrafast power diode in a SOT429 (3-lead TO-247) plastic package.

## 2. Features and benefits

- Low forward voltage drop
- Fast Switching
- Soft recovery characteristics
- High thermal cycling performance
- Low thermal resistance

## 3. Applications

- Telecom power supplies
- Welding machines
- Secondary rectification in SMPS

## 4. Quick reference data

Table 1. Quick reference data

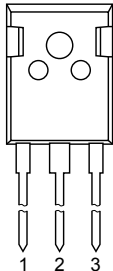
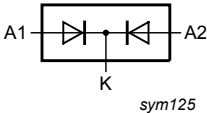
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage			-	-	300	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5 ; T <sub>mb</sub> ≤ 103 °C; square-wave pulse; per diode; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>		-	-	30	A
I <sub>O(AV)</sub>	average output current	δ = 0.5 ; T <sub>mb</sub> ≤ 103 °C; square-wave pulse; both diodes conducting		-	-	60	A
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5 ; t <sub>p</sub> = 25 μs; square-wave pulse; per diode		-	-	60	A
I <sub>FSM</sub>	non-repetitive peak forward current	t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 25 °C; sine-wave pulse; per diode; <a href="#">Fig. 4</a>		-	-	300	A
		t <sub>p</sub> = 8.3 ms; T <sub>j(init)</sub> = 25 °C; sine-wave pulse; per diode; <a href="#">Fig. 4</a>		-	-	330	A
Static characteristics							
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 6</a>		-	1	1.25	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <a href="#">Fig. 6</a>		-	0.85	1	V



Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Dynamic characteristics</b>						
$t_{rr}$	reverse recovery time	$I_F = 1\text{ A}$ ; $V_R = 30\text{ V}$ ; $dI_F/dt = 50\text{ A}/\mu\text{s}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>	-	-	50	ns
		$I_F = 30\text{ A}$ ; $V_R = 200\text{ V}$ ; $dI_F/dt = 200\text{ A}/\mu\text{s}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>	-	33	-	ns
		$I_F = 30\text{ A}$ ; $V_R = 200\text{ V}$ ; $dI_F/dt = 200\text{ A}/\mu\text{s}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>	-	62	-	ns

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	 <p><b>TO-247 (SOT429)</b></p>	 <p><i>sym125</i></p>
2	K	cathode		
3	A2	anode 2		
mb	K	mounting base; cathode		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYV430W-300P	TO-247	plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3 lead TO-247	SOT429

## 7. Marking

Table 4. Marking codes

Type number	Marking code
BYV430W-300P	BYV430W-300P

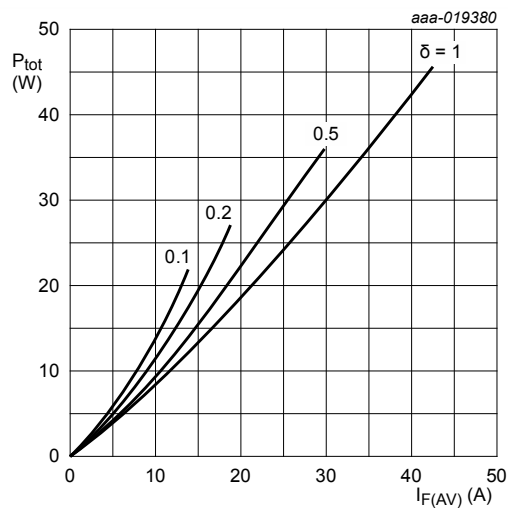


## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

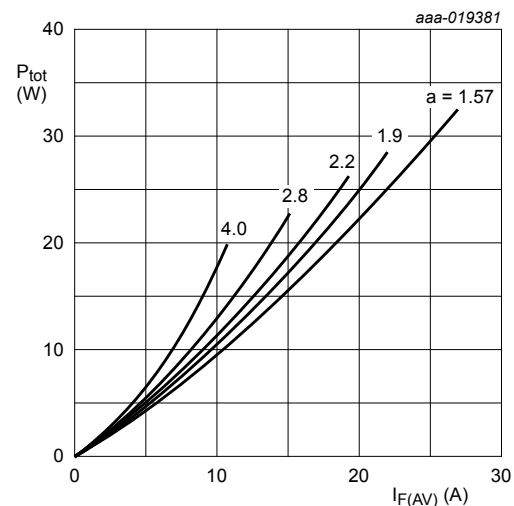
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	300	V
$V_{RWM}$	crest working reverse voltage		-	300	V
$V_R$	reverse voltage	DC	-	300	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$ ; $T_{mb} \leq 103^\circ\text{C}$ ; square-wave pulse; per diode; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	30	A
$I_{O(AV)}$	average output current	$\delta = 0.5$ ; $T_{mb} \leq 103^\circ\text{C}$ ; square-wave pulse; both diodes conducting	-	60	A
$I_{FRM}$	repetitive peak forward current	$\delta = 0.5$ ; $t_p = 25\text{ }\mu\text{s}$ ; square-wave pulse; per diode	-	60	A
$I_{FSM}$	non-repetitive peak forward current	$t_p = 10\text{ ms}$ ; $T_{j(\text{init})} = 25^\circ\text{C}$ ; sine-wave pulse; per diode; <a href="#">Fig. 4</a>	-	300	A
		$t_p = 8.3\text{ ms}$ ; $T_{j(\text{init})} = 25^\circ\text{C}$ ; sine-wave pulse; per diode; <a href="#">Fig. 4</a>	-	330	A
$T_{stg}$	storage temperature		-55	175	$^\circ\text{C}$
$T_j$	junction temperature		-	175	$^\circ\text{C}$



$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$

$$V_o = 0.817\text{ V}; R_s = 0.006\text{ }\Omega$$

**Fig. 1. Forward power dissipation as a function of average forward current; square waveform; per diode; maximum values**



$$a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$$

$$V_o = 0.817\text{ V}; R_s = 0.006\text{ }\Omega$$

**Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; per diode; maximum values**

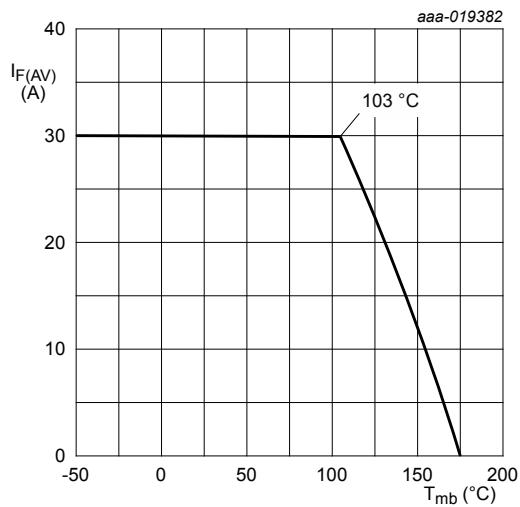


Fig. 3. Average forward current as a function of mounting base temperature; per diode; maximum values

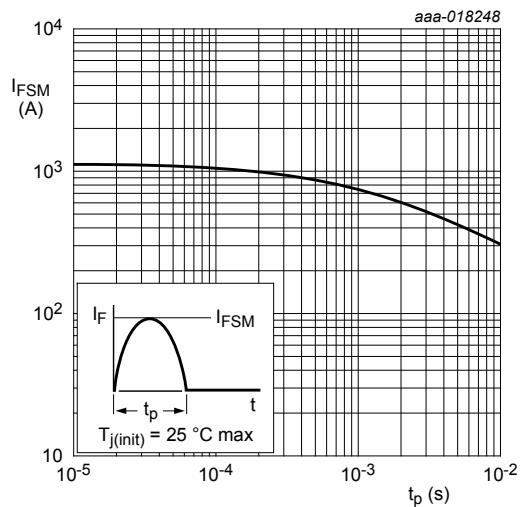
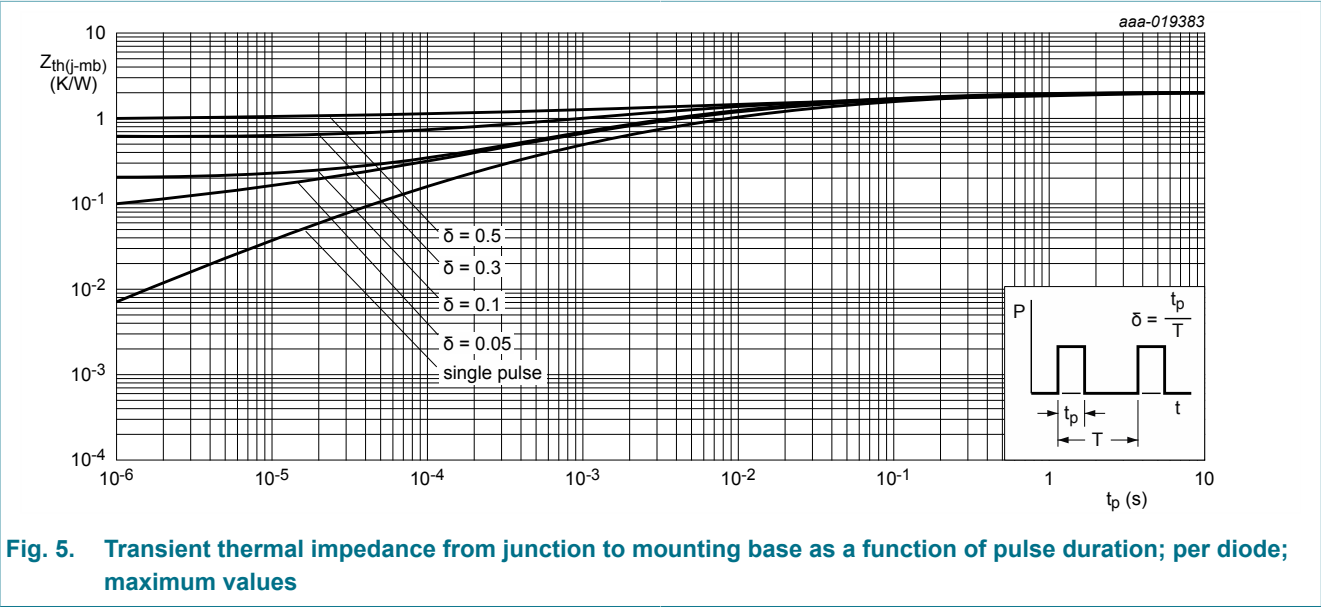


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; per diode; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	with heatsink compound; per diode; <a href="#">Fig. 5</a>	-	0.8	2	K/W
		with heatsink compound; both diodes conducting	-	-	1.2	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	-	45	-	K/W

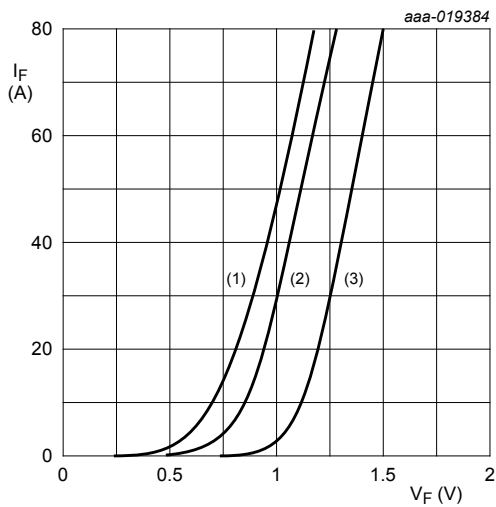


## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 6</a>		-	1	1.25	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <a href="#">Fig. 6</a>		-	0.85	1	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 300 V; T <sub>j</sub> = 25 °C		-	0.4	10	μA
		V <sub>R</sub> = 300 V; T <sub>j</sub> = 150 °C		-	-	500	μA
Dynamic characteristics							
Q <sub>r</sub>	recovered charge	I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>		-	89	-	nC
		I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 125 °C; <a href="#">Fig. 7</a>		-	337	-	nC
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 50 A/μs; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>		-	-	50	ns
		I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>		-	33	-	ns
		I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 125 °C; <a href="#">Fig. 7</a>		-	62	-	ns
I <sub>RM</sub>	peak reverse recovery current	I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>		-	5.3	-	A
		I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 125 °C; <a href="#">Fig. 7</a>		-	10.5	-	A





$V_o = 0.817\text{ V}; R_s = 0.006\text{ }\Omega$   
(1)  $T_j = 150\text{ }^\circ\text{C}$ ; typical values  
(2)  $T_j = 150\text{ }^\circ\text{C}$ ; maximum values  
(3)  $T_j = 25\text{ }^\circ\text{C}$ ; maximum values

Fig. 6. Forward current as a function of forward voltage, per diode

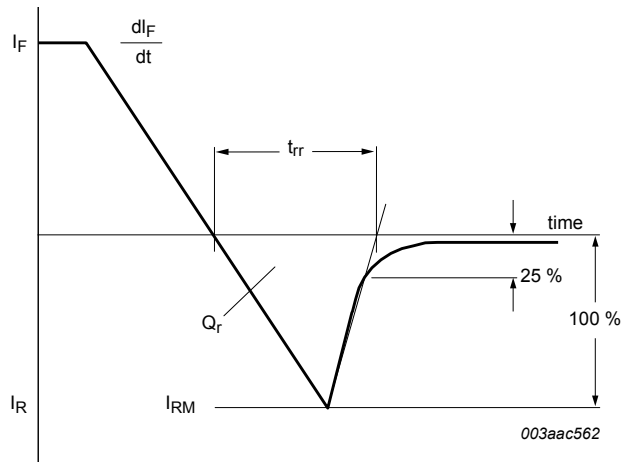


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline

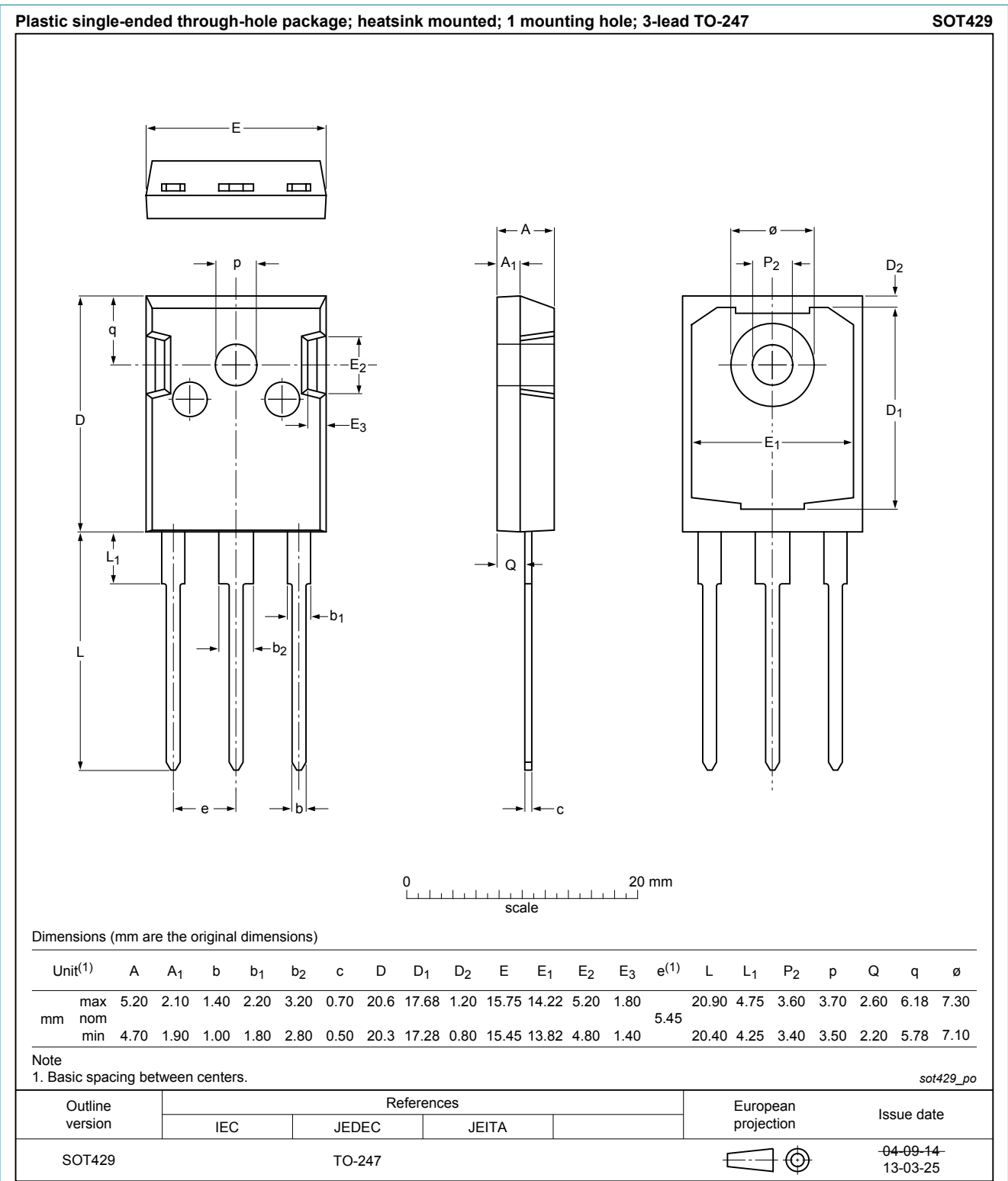


Fig. 8. Package outline TO-247 (SOT429)

## 12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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